



MBE SYSTEM AND SEMICONDUCTOR DEVICE FABRICATED, USING SAME

ABSTRACT OF THE DISCLOSURE

A molecular beam epitaxy system having a plurality of chambers which contain at least a first chamber and a second chamber. The first chamber is used to form II-V column compound semiconductor layers not containing Te. The second chamber is used to form II-V column compound semiconductor layers containing at least Te. A semiconductor device having an ohmic characteristics can be fabricated without mixing Te into other layers.

Figure 2